

BUK6212-40C

N-channel TrenchMOS intermediate level FET

Rev. 2 — 21 September 2010

Product data sheet

1. Product profile

1.1 General description

Intermediate level gate drive N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- AEC Q101 compliant
- Suitable for standard and logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoids
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$		-	-	40	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C};$ see <u>Figure 1</u>	[1]	-	-	50	Α
P _{tot}	total power dissipation	see Figure 2		-	-	80	W
Static char	Static characteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 12 \text{ A};$ $T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 11}}{\text{ or } 100 \text{ m}}$		-	9.5	11.2	mΩ



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 50 A; $V_{sup} \le$ 40 V; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped	-	-	55	mJ
Dynamic cl	Dynamic characteristics					
Q_{GD}	gate-drain charge	I_D = 25 A; V_{DS} = 32 V; V_{GS} = 10 V; see <u>Figure 13</u> ; see <u>Figure 14</u>	-	10.1	-	nC

^[1] Continuous current is limited by package.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		2
2	D	drain	mb	D
3	S	source		
mb	D	mounting base; connected to drain	1 3	mbb076 S
			SOT428 (DPAK)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK6212-40C	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	40	V
V_{GS}	gate-source voltage	Pulsed	<u>[1]</u>	-20	20	V
		DC	[2]	-16	16	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	[3]	-	50	Α
		T_{mb} = 100 °C; V_{GS} = 10 V; see Figure 1		-	41	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; $t_p \le 10 \mu s$; pulsed; see Figure 3		-	233	Α
P _{tot}	total power dissipation	see Figure 2		-	80	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drain	n diode					
Is	source current	T _{mb} = 25 °C	[3]	-	50	Α
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$		-	233	Α
Avalanche ru	uggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 50 A; $V_{sup} \le 40$ V; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	55	mJ
E _{DS(AL)R}	repetitive drain-source avalanche energy		[4][5][6]	-	-	J

^[1] Accumulated pulse duration not to exceed 5 minutes.

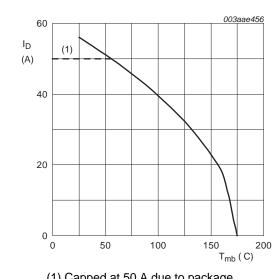
^{[2] -16}V accumulated duration not to exceed 168 hrs.

^[3] Continuous current is limited by package.

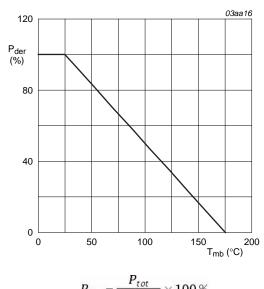
^[4] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

^[5] Repetitive avalanche rating limited by an average junction temperature of 170 °C.

^[6] Refer to application note AN10273 for further information.



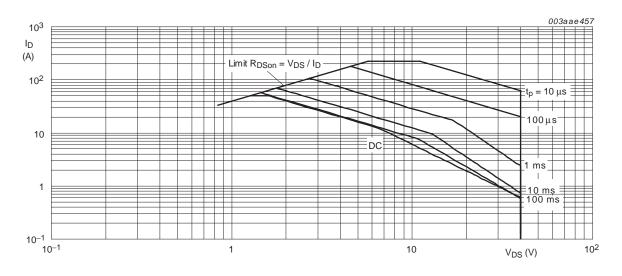
(1) Capped at 50 A due to package



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Continuous drain current as a function of Fig 1. mounting base temperature

Fig 2. Normalized total power dissipation as a function of mounting base temperature



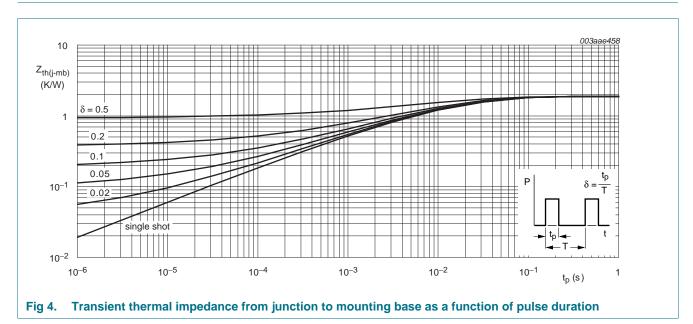
 T_{mb} = 25 °C; I_{DM} is a single pulse

Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	1.87	K/W



BUK6212-40C

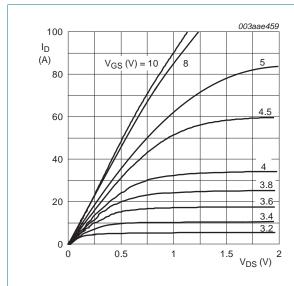
6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
$V_{(BR)DSS}$	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	40	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	36	-	-	V
$V_{GS(th)}$	V _{GS(th)} gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	1.8	2.3	2.8	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	-	-	3.3	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}$	0.8	-	-	V
I _{DSS}	drain leakage current	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μΑ
		$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
I _{GSS}	gate leakage current	$V_{DS} = 0 \text{ V}; V_{GS} = 20 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		$V_{DS} = 0 \text{ V}; V_{GS} = -20 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 12 \text{ A}; T_{mb} = 25 \text{ °C};$ see <u>Figure 11</u>	-	9.5	11.2	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 12 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 11</u>	-	13	16.3	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 12 \text{ A}; T_{mb} = 25 \text{ °C};$ see Figure 11	-	15	20	mΩ
		V_{GS} = 10 V; I_D = 12 A; T_j = 175 °C; see <u>Figure 12</u> ; see <u>Figure 11</u>	-	-	23.5	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}$; $V_{DS} = 32 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 13; see Figure 14	-	33.9	-	nC
		$I_D = 25 \text{ A}$; $V_{DS} = 32 \text{ V}$; $V_{GS} = 5 \text{ V}$; see Figure 13; see Figure 14	-	19.5	-	nC
Q_{GS}	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V};$	-	5.4	-	nC
Q_{GD}	gate-drain charge	see Figure 13; see Figure 14	-	10.1	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	1422	1900	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 15</u>	-	205	250	pF
C _{rss}	reverse transfer capacitance		-	143	200	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V};$	-	9.7	-	ns
t _r	rise time	$R_{G(ext)} = 10 \Omega$	-	21	-	ns
t _{d(off)}	turn-off delay time		-	54	-	ns
t _f	fall time		-	32	-	ns
L _D	internal drain inductance	measured from source lead to source bond pad; ; $T_j = 25 ^{\circ}\text{C}$	-	3.5	-	nΗ
L _S	internal source inductance	T _j = 25 °C; measured from drain to centre of die;	-	2.5	-	nΗ

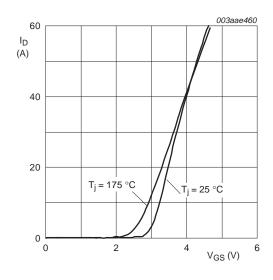
Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-drain	diode					
V _{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 16</u>	-	0.9	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$;	-	35.6	-	ns
Q _r	recovered charge	$V_{DS} = 25 \text{ V}$	-	38	-	nC



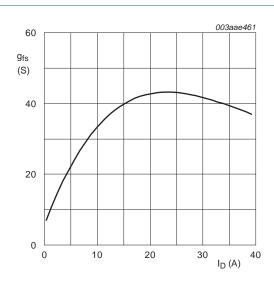
 $T_i = 25$ °C; $t_p = 300 \mu s$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



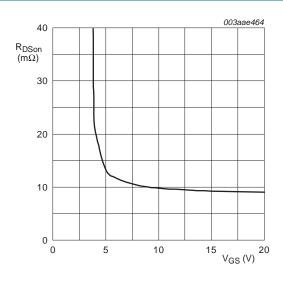
 $V_{DS} > I_D imes R_{DSon}$

Fig 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $T_j = 25$ °C; $V_{DS} = 25$ V

Fig 6. Forward transconductance as a function of drain current; typical values



 $T_j = 25$ °C; $I_D = 12$ A

Fig 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

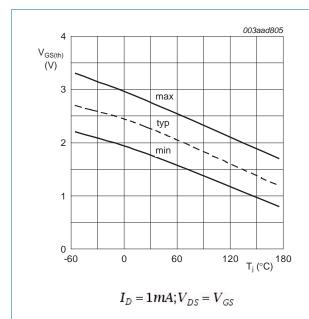


Fig 9. Gate-source threshold voltage as a function of junction temperature

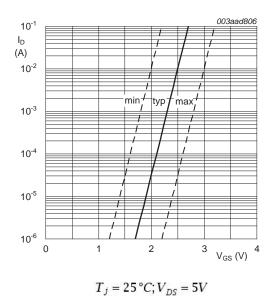


Fig 10. Sub-threshold drain current as a function of

gate-source voltage

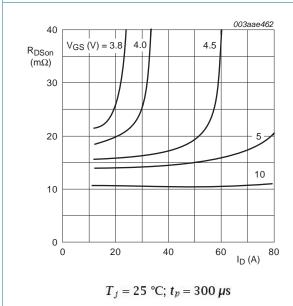


Fig 11. Drain-source on-state resistance as a function of drain current; typical values

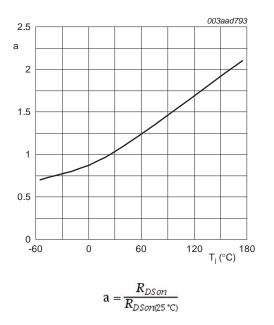
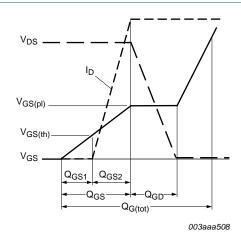


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

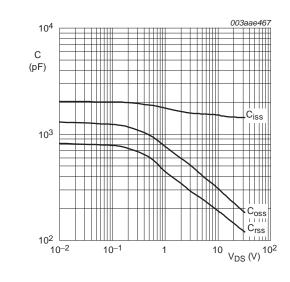


10 003aae466 VGS (V) 8 VDS = 14 V VDS = 32 V 4 QG (nC) 40

 $T_j = 25$ °C; $I_D = 25$ A

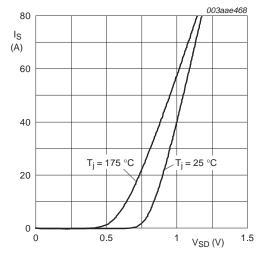
Fig 13. Gate charge waveform definitions





 $V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$

Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



 $V_{GS} = 0 \text{ V}$

Fig 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

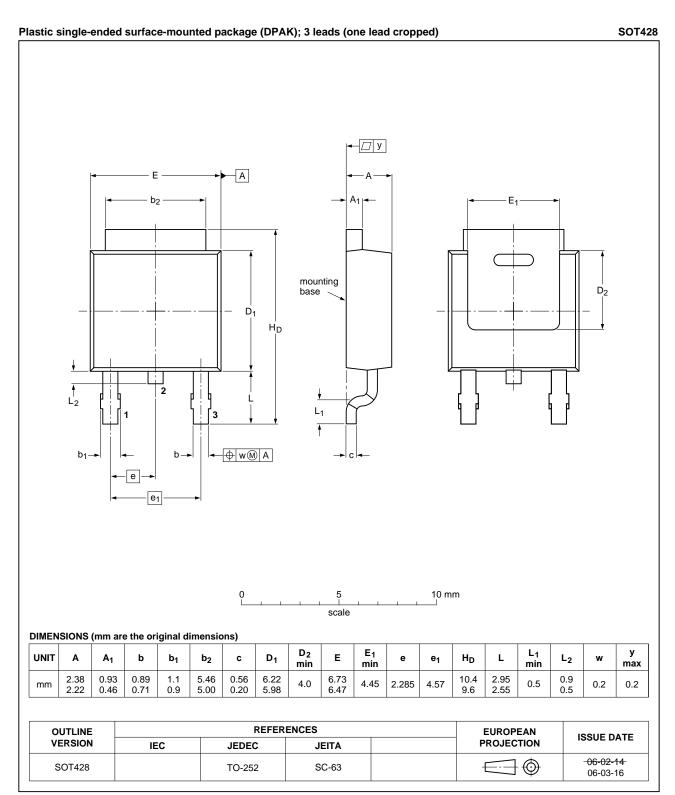


Fig 17. Package outline SOT428 (DPAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK6212-40C v.2	20100921	Product data sheet	-	BUK6212-40C v.1
Modifications: • Status changed from Objective to Product.				
	 Various chang 	es to content.		
BUK6212-40C v.1	20100512	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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